

AMENDMENTS

In the Claims:

Sub 7
In accordance with the examiner's request please delete the extraneous two lines that follow claim 10 and which are at the top of page 60 in the claims.

Please amend claims 1, 10, 19, 30, 32 and 33 as follows:

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1. (Twice Amended) A method for forming a compound semiconductor layer, comprising the step of crystal-growing a group III-V compound semiconductor layer containing at least nitrogen and arsenic as group V elements on a single crystal substrate,

wherein the step of crystal-growing the compound semiconductor layer includes the step of supplying an aluminum source material to the single crystal substrate concurrently with a nitrogen source material without pre-cracking.

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10. (Twice Amended) A method for forming a compound semiconductor layer, comprising the step of crystal-growing a group III-V compound semiconductor layer containing at least nitrogen and arsenic as group V elements on a single crystal substrate,

wherein the step of crystal-growing the compound semiconductor layer includes the step of supplying a nitrogen source material without pre-cracking to the single crystal substrate so that the nitrogen source material interacts with aluminum at least on a crystal growth surface of the compound semiconductor layer.

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19. (Amended) A method for forming a compound semiconductor layer, comprising the step of crystal-growing a group III-V compound semiconductor layer containing at least nitrogen and arsenic as group V elements on a single crystal substrate,

wherein the step of crystal-growing the compound semiconductor layer includes the step of supplying a nitrogen source material without pre-cracking to a crystal surface of the

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compound semiconductor layer in a state where the group III atoms containing aluminum are exposed to the crystal surface.

30. (Twice Amended) A compound semiconductor apparatus, comprising at least one group III-V compound semiconductor layer containing at least aluminum as a group III element and containing at least nitrogen and arsenic as group V elements, wherein an Al-mix crystal ratio X in the layer is 0.02 or higher and 0.20 or lower.

32. (Amended) A compound semiconductor apparatus, comprising at least one group III-V compound semiconductor layer containing at least aluminum as a group III element and containing at least nitrogen and arsenic as group V elements; and

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wherein the compound semiconductor apparatus is a light emitting device including at least a light emitting layer, and the light emitting layer includes the compound semiconductor layer; and

wherein the light emitting layer is formed of $\text{Al}_x\text{Ga}_y\text{In}_{1-x-y}\text{N}_z\text{As}_{1-z}$ ($0 < x, y, z < 1$), wherein an Al-mix crystal ratio x in the light emitting layer is 0.02 or higher and 0.20 or lower.

33. (Amended) A compound semiconductor apparatus according to claim 32, wherein the light emitting device further includes a cladding layer, a guide layer and/or a barrier layer formed of $\text{Al}_h\text{Ga}_i\text{In}_{1-h-i}\text{As}_j\text{P}_{1-j}$ ($h \geq 0, i > 0, j \geq 0$).